

Form PTO-1449
(Rev. 8-83)Department of Commerce
Patent and Trademark Office

Atty Docket 0756

Serial No. 09/837,552

INFORMATION DISCLOSURE STATEMENT

Applicants: Hisashi OHTANI et al.

Filing Date: April 19, 2001

Group Art Unit:
Unassigned

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
NDR	4,748,485	05/31/1988	Vasudev			
NDR	4,977,105	12/11/1990	Okamoto et al.			
NDR	4,984,033	01/08/1991	Ishizu et al.			
NDR	4,996,575	02/26/1991	Ipri et al.			
NDR	5,034,788	07/23/1991	Kerr			
NDR	5,103,277	04/07/1992	Caviglia et al.			
NDR	5,124,769	06/23/1992	Tanaka et al.			
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NDR	5,198,379	03/30/1993	Adan			
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NDR	5,246,882	09/21/1993	Hartmann			
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Examiner

Date Considered

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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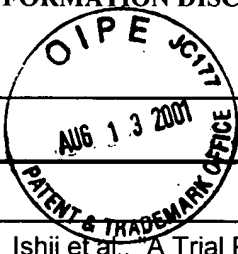
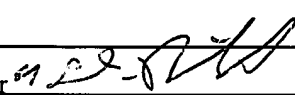
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes	No
NDR	0 178 447	04/23/1986	EP			Full Eng	
NDR	01-059866	03/07/1989	JP			Eng Abst	
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Examiner	Date Considered 6/30/02

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INFORMATION DISCLOSURE STATEMENT 				Applicants: Hisashi OHTANI et al.	
				Filing Date: April 19, 2001	Group Art Unit: Unassigned
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)					
Examiner Initial					
non	Ishii et al., "A Trial Product of Dual-Gate MOS (X MOS) Device", pp. 405, 1985, 46th Japan Society of Applied Physics, 2a-V-9				
non	Ishii et al., "Experimental Fabrication of XMOS Transistors Using Lateral Solid-Phase Epitaxy of CVD Silicon Films", pp. L521-L523, April 1990, Japanese Journal of Applied Physics, Vol. 29, No. 4				
non	Noguchi et al., "Advanced High Mobility Polysilicon Super-thin Film Transistor (SFT) Using Solid Phase Growth", pp. 549-552, 1986, Extended Abstracts of the 18th International Conference on Solid State Devices and Materials, Tokyo, B-10-2				
non	Hayashi et al., "Polysilicon Super-Thin-Film Transistor (SFT)", pp. L819-L820, November 1984, Japanese Journal of Applied Physics, Vol. 23, No. 11				
non	Hayashi et al., "High Performance Superthin Film Transistor (SFT) with Twin Gates", pp. 59-62, 1987, Extended Abstracts of the 19th Conference on Solid State Devices and Materials, Tokyo, A-3-5				
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non	Tuan et al., "Dual-Gate a-Si:H Thin Film Transistors", pp. 357-359, December 1982, IEEE Electron Device Letters, Vol. EDL-3, No. 12				
non	Specifications and Drawings for Patent Application Serial No. 09/837,877, "Semiconductor Device", Filing Date: April 19, 2001, Shunpei YAMAZAKI et al.				
non	Specifications and Drawings for Patent Application Serial No. 09/837,558, "Semiconductor Device and Manufacturing Method Thereof", Filing Date: April 19, 2001, Shunpei YAMAZAKI et al.				
Examiner					Date Considered 10/1/03

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Substitute for form 1449A/PTO				<div style="text-align: right;"><i>Complete if Known</i></div>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	09/837,552
				Filing Date	April 19, 2001
				First Named Inventor	Hisashi OHTANI et al.
				Group Art Unit	Unassigned
				Examiner Name	Unassigned
				Attorney Docket Number	0756-2296
Sheet	1	of	1		

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	<i>[Signature]</i>	Date Considered	6/30/02
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

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